

07/11/2001
07/11/2001
PTO-1449

Form PTO-1449		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO MI221657	SERIAL NO Unknown
LIST OF ART CITED BY APPLICANT Use several sheets if necessary.				APPLICANT Cem Bascer et al	
				FILING DATE Filed Herewith	GROUP Unknown

U. S. PATENT DOCUMENTS

*Examiner Name		Document Number	Date	Name	Class	Subclass	Filing Date * Appropriate
EE	AA			Cem Bascer et al as filed			Filed Contemporaneously
EE	AB	09 476 516		Cem Bascer as filed and as amended			01 03 00
EE	AC	09 580 733		Cem Bascer as filed			05 26 00
EE	AD	5 459 635	10 17 95	Tomozawa et al	361	321.5	
EE	AE	5 618 761	04 08 97	Eguchi et al	438	785	
	AF						
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
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	AO							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER <i>J. K. K. K.</i>	DATE CONSIDERED 12/04/01
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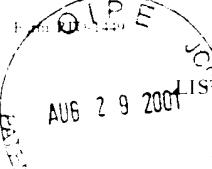
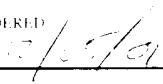
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Ex-AMR 1249		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-5057	SERIAL NO. 09/608,320		
AUG 29 2001		LIST OF ART CITED BY APPLICANT Use several sheets if necessary		APPLICANT Cem Basceri et al.			
				FILING DATE July 13, 2001	GROUP Unknown		
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
E	AA	5,286,485	10/26/93	Numasawa			
E	AB	5,731,948	01/21/97	Endo			
E	AC	5,726,254	03/24/98	Yildiz et al			
E	AD	5,783,253	07/07/98	Yuuki et al			
E	AE	5,708,904	07/21/98	Roh			
E	AF	6,043,526	08/25/98	Dhote et al			
E	AG	6,046,349	03/28/00	Ochiai			
E	AH	6,078,492	04/04/00	Kadokura et al			
E	AI	6,153,898	06/20/00	Huang et al			
E	AJ	6,037,205	11/28/00	Watanabe			
E	AK	6,037,205	03/14/00	Huh et al			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes <input type="checkbox"/> No <input type="checkbox"/>
E	AL	0-855-715-A2	26/01/98	EPO - Zhao et al., Applied Materials, Inc.			
E	AM	0-957-522-A2	12/05/99	EPO - Ueda, Michihito, Matsushita Electric Ind. Co.,			
E	AN	WO 98/0497	20/02/98	WIPO - Simpson, John et al			
E	AO	0-474-140-A1	30/08/91	EPO - Kamiyama, Satoshi c/o NEC Corporation			
E	AP	WO 99/64645	11/06/99	WIPO - Narwankar et al., Applied Materials, Inc.			
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
E	AR	Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD BaSr_xTiO₃</i> , pp. 1-21 (MRS Fall Meeting 12/01/94)					
E	AS	Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 pages					
E	AT	Y. C. Chen et al., Abstract, <i>Improvements of the Properties of Chemical Vapor-Deposited (Ba,Sr,Ti)O₃ Films Through Use of a Seed Layer</i> , J. Jpn. J. Appl. Phys. Pt. 1, No. 31, pp. 6824-6828 (1992)					
EXAMINER	<i>C. J. Clark</i>		DATE CONSIDERED 1/26/01				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-154 OCT-5-2001 AUG 29 2001		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1657	SERIAL NO. 09/908,320		
		LIST OF ART CITED BY APPLICANT Use several sheets if necessary		APPLICANT Cem Bascer et al.	FILING DATE July 15, 2001	GROUP U.S. & W.	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
EF	5,470,398	11/28/95	Shibuya et al.				
EF	5,254,805	10/19/93	Kamiyama				
EF	6,156,638	12/05/00	Agarwal et al.				
EF	6,165,834	12/26/00	Agarwal et al.				
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AI						Yes	No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EF	AF		Chung Ming Chu et al., Abstract, <i>Electrical properties and crystal structure of (Ba/Sr)TiO₃ films prepared at low temperatures on a LaNiO₃ electrode by radio-frequency magnetron ...</i> , 70 APPLIED PHYSICS LETTERS, Nov. 2, pp. 249-251 (1997)				
EF	AS		Kazuhiko Eguchi et al., Abstract, <i>Chemical vapor deposition of (Ba/Sr)TiO₃ thin films for application in great scale dynamic random access memory</i> , 14 INTEGRATED FERRO-ELECTRICS Nos. 1-4, Pt. 1, pp. 33-42 (1997)				
EF	AF		Q-X. Jia et al., Abstract, <i>Structural and dielectric properties of Ba/Sr thin films with an epit RuO₂ bottom electrode</i> , 19 INTEGRATED FERRO-ELECTRICS Nos. 1-4, pp. 111-119 (1998)				
EXAMINER <i>C. Zeller</i>			DATE CONSIDERED <i>12/05/01</i>				
*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

<p style="text-align: center;">AUG 29 2001 LIST OF ART CITED BY APPLICANT Use several sheets if necessary</p>		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1657	SERIAL NO. 09/965,320	
		APPLICANT Cem Basceri et al.				
		FILING DATE July 13, 2001		GROUP Unknown		
		U. S. PATENT DOCUMENTS				
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	Document Number	Date	Country	Class	Subclass	Translation
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)						
EF	AR	Takuaki Kawahara et al., <i>(Ba, Sr)TiO_x Films Prepared by Liquid-Source Chemical Vapor Deposition on Ru Electrodes</i> , 35 JPN. J. APPL. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).				
EF	AS	Rajesh Khamankar et al., <i>A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM Applications</i> , Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages				
EF	AT	Yong Tae Kim et al., Abstract, <i>Advantages of RuO_x bottom electrode in the dielectric and leakage characteristics of BaSrTiO_x capacitor</i> , 35 JPN. J. APPL. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).				
EXAMINER			DATE CONSIDERED			
<i>C. E. C.</i>			<i>12/05/01</i>			
<p>*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>						

Form PTO-144		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			AFFY. DOCKET NO. M122-1657		SERIAL NO. 09/908,520		
LIST OF ART CITED BY APPLICANT Use several sheets if necessary			APPLICANT Cem Basceri et al.						
AUG 29 2001			FILING DATE July 15, 2001			GROUP 1-875-A			
U. S. PATENT DOCUMENTS									
* Examiner Initial	Document Number	Date	Name			Class	Subclass	Filing Date is P. Appropriate	
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EF	AR		S.H. Park et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering</i> .						
			Ferroelectric Thin Films V Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995)						
EF	AS		N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba_xSr_{1-x}TiO₃</i> , 98 NIPPON						
			SEKAMIKKAI KYOKAI GAKKUTSU RONBUNSHI No. 8, pp. 836-839 (1996)						
EF	AT		H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO₃, BaTiO₃ thin films</i> , IEEE						
			International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992)						
EXAMINER <i>C. Trulke</i>			DATE CONSIDERED <i>12/15/01</i>						
*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

 LIST OF ART CITED BY APPLICANT <small>Use several sheets if necessary</small>		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		AUTY DOCKET NO. MI22 1657		SERIAL NO. 09/905,320			
		APPLICANT Cen. Biscetti et al.		FILING DATE July 15, 2003		GROUP Unknown			
		U.S. PATENT DOCUMENTS							
		Examiner Initials	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
	AR		S. Yamamichi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba, Sr, TiO) thin films prepared</i>						
			<i>by ion-beam sputtering</i> , 64 APPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994)						
	AS		M. Yamamaka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr,TiO) Thin Films Prepared by Chemical-Vapor-Deposition</i> ,						
			35 JPN. J. OF APPL. PHYS. Pt. 1, No. 2A, pp. 729-735 (1996)						
	AT		Arai T., et al. <i>Preparation of SrTiO₃ Films on 8-Inch Wafers by Chemical-Vapor Deposition</i> , Jpn. Journal of Applied Physics, Vol. 35,						
			N. 9B, Part 1, 09/01/96, Pg. 4875-4879						
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<small>*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>									

Form PTO-1449		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			APPLY. DOCKET NO. M122/687		SERIAL NO. 09/063,329		
AUG 29 2001 LIST OF ART CITED BY APPLICANT Use several sheets if necessary					APPLICANT Cem Basceri et al.				
					FILING DATE July 13, 2001		GROUP Unknown		
U. S. PATENT DOCUMENTS									
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
CF	AR		Kim, et al. <i>Structural and Electrical Properties of BaTiO₃ grown on p-InP (100) by low-pressure metalorganic chemical vapor deposition at low temperature</i> . Applied Physics Letters, US, American Institute of Physics Vol. 65, No. 15, 10/10/94, Pgs. 1955-1957						
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EXAMINER			DATE CONSIDERED						
<i>E. Delle</i>			<i>12/03/01</i>						
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